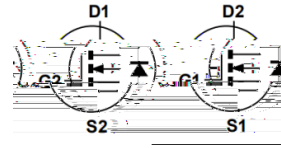




Product Summary

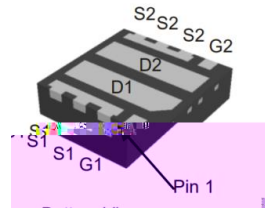
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.



Trench technology

$R_{DS(ON)}$ to minimize conductive loss

Dual DIE in one package



Power Management in Notebook Computer,
Portable Equipment and Battery Powered
Systems

Part NO.	ZMD68602M
Marking	68602
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	20	A
	$I_{D@TC=75}$	15	A
	$I_{D@TC=100}$	12	A
Pulsed Drain Current	I_{DM}	40	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	20	W
Total Power Dissipation($TA=25$)	$P_D@TA=25$	1.7	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	90	mJ



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
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Fig.7 Switching Time Measurement Circuit

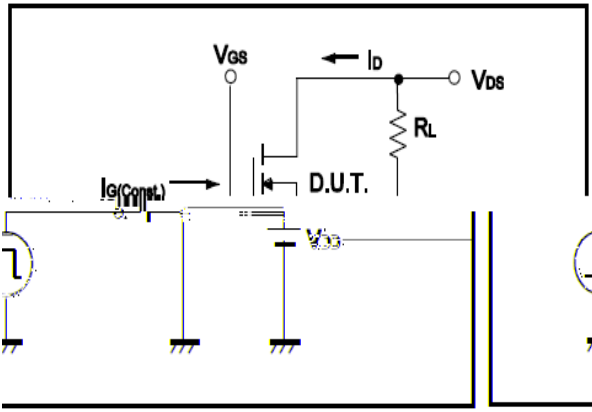


Fig.8 Gate Charge Waveform

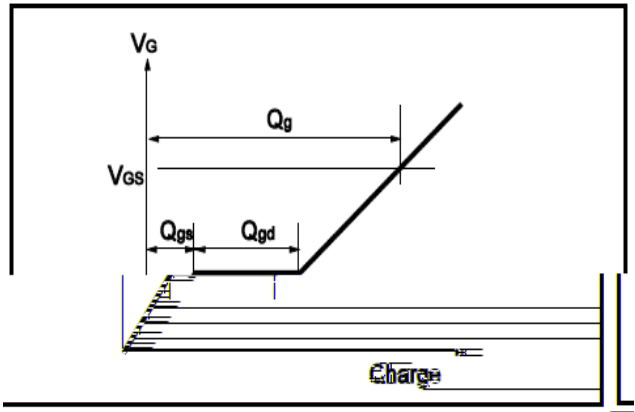


Fig.9 Switching Time Measurement Circuit

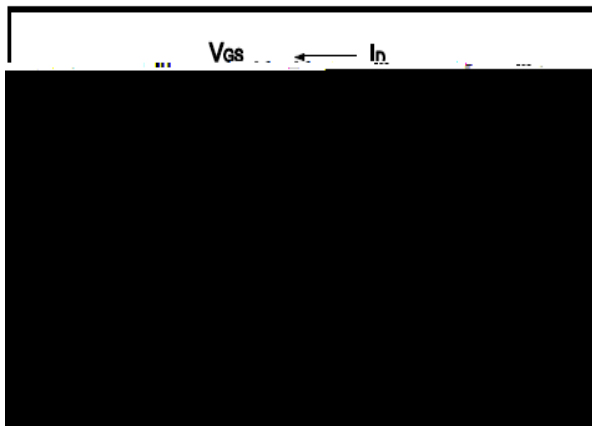


Fig.10 Gate Charge Waveform

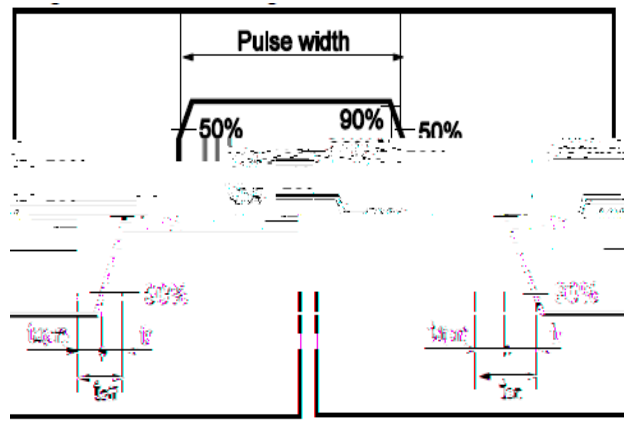


Fig.11 Avalanche Measurement Circuit

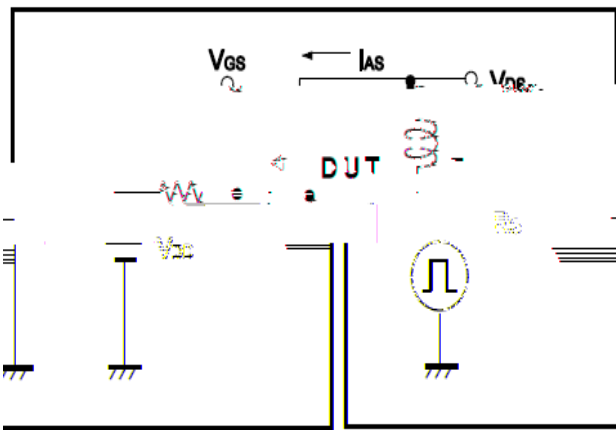


Fig.12 Avalanche Waveform

